G round state cooling of mechanical resonators

Ivar M artin¹, A lexander Shnirm an², Lin Tian^{3;4}, and Peter Zoller^{3;4}

¹Theoretical D ivision, Los A lam os N ational Laboratory, Los A lam os, NM 87545, USA

²Institut fur Theoretische Festkorperphysik, Universitat K arlsruhe, D-76128 K arlsruhe, G erm any

³Institute for Theoretical Physics, University of Innsbruck, A-6020, Austria

⁴Institute for Quantum Optics and Quantum Information of the Austrian Academy of Sciences, 6020 Innsbruck, Austria

We propose an application of a single Cooper pair box (Josephson qubit) for active cooling of nanom echanical resonators. Latest experiments with Josephson qubits demonstrated that long coherence time of the order of microsecond can be achieved in special symmetry points. Here we show that this level of coherence is su cient to perform an analog of the well known in quantum optics \laser" cooling of a nanom echanical resonator capacitively coupled to the qubit. By applying an AC driving to the qubit or the resonator, resonators with frequency of order 100 M H z and quality factors higher than 10^3 can be e ciently cooled down to their ground state, while lower frequency resonators can be cooled down to micro-Kelvin temperatures. We also consider an alternative setup where DC-voltage-induced Josephson oscillations play the role of the AC driving and show that cooling is possible in this case as well.

INTRODUCTION

Recently, fabrication of nanomechanical resonators with fundamental frequencies in the microwave range (100 M H z to 1G H z) has been achieved [1]. For such resonators, the quantum mechanical level spacing is a few m icro-eV, which is comparable to the lowest achievable cryogenic tem peratures. Freezing out the mechanical degrees of freedom is favorable for ultra sensitive detection applications [2] due to reduced e ects of therm al uctuations. Even more spectacular applications can be envisioned if it is possible to cool the mechanical systems down to theirm otional ground states with high probability. C reation of exotic non-classical states, entanglem ent with other quantum objects, e.g. spins or atoms, coherent quantum information transfer between quantum sub-systems are just a few possibilities. However, reaching the motional ground state using conventional passive cooling techniques is practically unfeasible, and therefore other approaches need to be explored. Fortunately, the cooling problem is not unique to nanomechanics; a similar problem has been encountered and successfully solved in the eld of ultra-cold atoms, where by using active cooling approaches it was possible to quench the vibrational motion of atoms and reach elective nano-Kelvin tem peratures [3]. The connection to quantum optics has been recently explored in several works. Hopkins et al. [4] applied the quantum feedback control ideas to nanom echanical resonator cooling. Wilson-Rae et al. [5] proposed an analogue of resolved sideband laser cooling by coupling the resonator displacem ent to the level spacing of an attached sem iconductor quantum dot, which is being irradiated by red-detuned laser. An advantage over the feedback-based techniques is that the sideband cooling does not require on-the-y analysis of the output of a nearly ideal detector. On the other hand, direct im plem entation of the Ref. [5] approach appears rather challenging, from the fabrication stand point and due to

stringent constraints on the quantum dot relaxation rate, which needs to be slower than the resonator frequency for the vibrational sidebands to be resolved.

In this work we study an alternative realization of the laser-like cooling for nanom echanical resonators, where the role of the two-state system is played by a superconducting qubit (Cooper Pair Box, or CPB) capacitively coupled to the resonator. Interaction between the qubit and the resonator leads to splitting of the qubit states into equidistant vibrational sidebands. Latest experiments with Josephson qubits showed that long coherence time of the order of microsecond can be achieved in special symmetry points [6]. When the qubit relaxation and dephasing rates are smaller than the oscillator frequency, one reaches the resolved sideband regim e, favorable for cooling. By tuning microwave source frequency into the rst red sideband (qubit level spacing m inus the oscillator frequency), one can ensure that the m icrow ave photon absorption processes are preferentially accompanied by simultaneous phonon emission from the resonator. The cooling cycle is completed when a photon is spontaneously em itted at the qubit natural frequency into an external bath. The em itted photon is blue-shifted relative to the source, as it carries away one resonator phonon energy. The exact reverse of this process is exponentially suppressed if the qubit level spacing is large relative to tem perature, and hence the heating is determ ined by other { non-resonant or driving-induced { processes which are much slower than the dominant cooling mechanism. This makes cooling possible. A suggestion to use coupled nanoresonator-qubit system for laser-like cooling has been rst made by Irish and Schwab [7]. Here we consider two implementation of this scheme that use di erent AC driving sources: (1) m icrow aves directly applied to the CPB or the resonator, in the form of AC ux or voltage; (2) the AC Josephson e ect on an auxiliary Josephson junction of the qubit. The advantage of the second approach is that it only requires DC bias

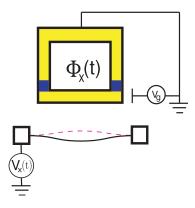


FIG. 1: The system with AC driving.

for cooling; however, we not that it is not as elective as the AC biasing scheme. In the opposite lim it of fast CPB relaxation when the vibrational sidebands are not resolved, we demonstrate that another type of laser cooling, \Doppler" cooling [3], can be performed down to the temperature dened by the quantum dot level width. A lithough ground state cooling in this regime is impossible, this technique could be practically attractive for noise reduction in local probe applications (e.g., AFM, MFM, and MRFM), where typical resonator frequencies are below 1 MHz.

AC COOLING

System . The system under consideration is shown in Fig.1. A mechanical resonator (horizontal beam) is coupled to a Cooperpair box (yellow rectangle) through capacitance C_x (x), which depends on the resonator displacement x. The charge, and hence the state, of CPB is separately controlled by the gate voltage V_g applied to capacitor C_g . CPB is coupled to a large superconductor through two Josephson junctions. The SQUID geometry is chosen to allow for application of an external AC ux to the system to provide the AC driving needed for cooling. Similar systems were considered in Refs. [7,8]. The Hamiltonian of the system without dissipation reads

$$H = \frac{(Q - C_gV_g - C_x(x)V_x)^2}{2C} - E_J(x) \cos + H_x; (1)$$

where Q is the charge on the island, C $_{\rm C}$ C + C $_{\rm g}$ + C $_{\rm x}$ (x) is the total capacitance of the island, and H $_{\rm x}$ $\frac{p^2}{2m}$ + $\frac{m+\frac{2}{0}x^2}{2}$. The total Josephson energy of the SQUID controlled by an external ux $_{\rm x}$ is given by E $_{\rm J}$ ($_{\rm x}$) = 2E $_{\rm J}^0$ cos($_{\rm x}$ = $_{\rm 0}$), where E $_{\rm J}^0$ is the Josephson energy of each of the junctions (we consider a symmetric setup) and $_{\rm 0}$ = h=2e is the (superconducting) ux quantum . We assume the total gate charge Q $_{\rm g}$ C $_{\rm g}$ V $_{\rm g}$ + C $_{\rm x}$ (x)V $_{\rm x}$ to be close to an odd number of electron charges, i.e., Q $_{\rm g}$ = 2e(N + 1=2) + 2e N , where j N j 1=2. Then we

can use a two state approximation, i.e., j"i $\mathfrak{D}=2eN$ i and j#i $\mathfrak{D}=2e(N+1)$ i and rewrite the Ham iltonian using the Paulimatrices as

$$H = 4E_{C}(x) N(x)_{z} + E_{C}(x)(1 + 4 N^{2}(x))$$

$$\frac{E_{J}}{2}_{x} + H_{x}; \qquad (2)$$

where $E_{\rm C}$ (x) \hat{e} =2C . The second term in the rst line of Eq. (2) depends on x and, thus, added to the oscillator H am iltonian H $_{\rm X}$, renormalizes (slightly) the oscillator parameters. This term is also responsible for the direct coupling of the oscillator to the dissipation in the circuitry (see below). We, rst, drop this term for clarity but later reintroduce it when discussing the direct coupling between the oscillator and the gate voltage uctuations. Assuming that uctuations of x are small relative to the resonator-CPB distance d, we obtain $C_{\rm X}$ (x) $C_{\rm X}$ $C_{\rm X}$ x=d. Thus N (x) N Nx=d, where N $_{\rm X}$ $C_{\rm X}$ $V_{\rm X}$ =2e, and E $_{\rm C}$ (x) $E_{\rm C}$ + E $_{\rm C}$ ($C_{\rm X}$ = $C_{\rm C}$) (x=d). Then the H am iltonian simplies to

$$H = 4E_C N_z \frac{E_J}{2}_x + (a^y + a)_z + h!_0 a^y a;$$
 (3)

where $h=(2m !_0)$ is the amplitude of zero point motion, x=x (a ^y+a). To increase the coupling one usually applies high gate voltage V_x so that N_x 1. Thus, approximately

$$4E_0 N_x \frac{x}{d}$$
: (4)

Both gate voltages, V_g and V_x , as well as the external ux $_x$ uctuate as they are provided by dissipative sources. This makes n and E_J in Eq. (3) uctuate. Moreover, in all real systems there are 1=f charge and ux noises. The charge 1=f noise can extrively be added to the noise of the gate charge N. Experimentally, 1=f noise is the most severe factor limiting coherence. Long coherence times have been achieved in Ref. [6] by operating in a special point where the 1=f noise is less harm ful. In the special point, the total energy splitting of the qubit $E = \frac{(8E_C)^2}{(8E_C)^2} \frac{N^2 + E_J^2}{N^2 + E_J^2}$ is not sensitive to the uctuations of N and $_x$ in the linear order. This implies h N i = 0 and $(8E_J = 0)$ The uctuations of N are, nevertheless, still there and we obtain the following H am iltonian characterizing the special point

$$H = \frac{E_J}{2} _{x} + h!_{0}a^{y}a + (a^{y} + a) _{z}$$

$$\frac{X}{2} _{z} + g (a^{y} + a) X ; \qquad (5)$$

where X $\frac{4E_c}{e}$ (C_g V_g + C_x V_x). By construction the coupling constant also contains a uctuating part. We neglect this higher order e ect. The uctuations of voltages V_g and V_x are caused by external

im pedances Z (!) of the circuits that supply the voltages. The (unsym m etrized) noise power is given by h V_i^2 i h V (t) V (0) $\dot{\mathbf{i}} = \mathbb{R} \, e\mathbb{Z} \, (!) \, \mathbb{h} \, ! \, (\coth (h! = 2k_B \, T) + 1) . \, Thus$ the term $X_z=2$ represents the coupling of the system to the harm onic (Gaussian) electrom agnetic bath. The situation is similar to the quantum optics one where an atom is coupled to electrom agnetic vacuum. The main di erences are that in our case the coupling is longitudinal, i.e., it does not cause spin ips in the natural (charge) basis, and the bath temperature cannot always be neglected. The last term in Eq. (5) is the direct coupling between the bath and the oscillator. It originates from the second term in Eq. (2), and $g = N_x x=d$ at the sym metry point. In the weak coupling case that we consider, the bath is fully characterized by its spectral function, and hence we do not need to include the self-H am iltonian of the bath explicitly. The non-electrom agnetic bath acting on the resonator is later introduced through a phenom enologicalquality factor Q.

Equilibrium transition rates. To proceed, we rst need to determ ine the resonator-qubit system relaxation rates caused by the electrom agnetic environment. It is convenient to perform a =2 rotation in the x z plane, x \hat{x} z, to the eigenbasis of the qubit at the sym m etry point. The H am iltonian becomes

$$H = \frac{E_J}{2} z + h!_0 a^y a + (a^y + a) x$$

$$\frac{X}{2} x + g (a^y + a) X : \qquad (6)$$

We choose E_J !0; ;T. This ensures that without the driving the spin is all the time in the ground state j'i. The qubit relaxation rate is

r #! " =
$$\frac{hX_{!=E_J}^2 \dot{1}}{4h^2}$$
 gE_J; (7)

where hX $_{!}^{2}i = 2 h^{2}_{g}!$ [coth (h!=2k_BT) + 1], $_{g}$ $\frac{C_{x}^{2}+C_{g}^{2}}{C^{2}}\frac{R}{R_{Q}}$, R_{Q} h=4e (here we assumed independent V_{g} and V_{x} with similar external in pedances ReZ (!) R 50). The opposite excitation rate is exponentially suppressed.

The direct coupling between the bath and the oscillator gives the dissipative rates between the oscillator states jni: $_{n! \ n-1}$ $g^2hX_{!=!_0}^2$ in= h^2 and $_{n! \ n+1}$ $g^2hX_{!=!_0}^2$ i(n + 1)= h^2 . In addition, the oscillator can relax via the virtual excitations of the qubit. The corresponding processes are shown in Fig. 2. The rates for these processes are given by

$$n! \ n \ 1 \ \frac{2}{E_J^2} \frac{hX_{!=!_0}^2 \dot{1}}{4h^2} n ;$$
 (8)

$$_{n! n+1} = \frac{^{2}}{E_{J}^{2}} \frac{hX_{!=.!_{0}}^{2} \dot{1}}{4h^{2}} (n+1) :$$
 (9)

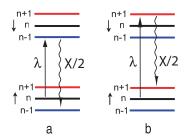


FIG. 2: D issipative processes due to the presence of the qubit: a) $n \cdot n \cdot 1$; b) $n \cdot n \cdot 1$. The spectra of the oscillator and the qubit are superim posed.

These rates are bigger than those due to the direct coupling by a factor $(2E_C = E_J)^2$, and hence the direct coupling term in the Ham iltonian (/ g) can be discarded. The above transition rates translate into the resonator quality factor caused by the coupling to the electrom agnetic bath,

$$\frac{1}{Q_{\text{em}}} = \frac{2}{E_{.T}^2} g: \qquad (10)$$

The charge noise at the (relatively low) frequency $!=!_0$ may be dominated by the 1=f contribution. The sym metrized correlator of this contribution has been studied, e.g., in echo experiments [9], and one can assume S_X (!) = $(hX_{\cdot}^2i+hX_{\cdot}^2i)=2=E_{1=f}^2=j!$ j, where $E_{1=f}=4E_C^p$ and typically $_{1=f}=10^7$. We are not aware of any study of the unsymmetrized correlators. Thus, we will introduce a phenomenological temperature $T_{1=f}$ for the particular frequency $!=!_0$ via $\exp h!_0=(k_BT_{1=f})$ $hX_{\cdot}^2i_0=hX_{\cdot}^2i_0$. Then, for the corresponding quality factor we obtain

$$\frac{1}{Q_{1=f}} \quad \frac{2}{E_J^2} \frac{8E_C^2}{(h!_0)^2} \quad _{1=f} \tanh \frac{h!_0}{2k_B T_{1=f}} : \quad (11)$$

It is reasonable to assume that the elective 1=f noise temperature is not lower than the environment temperature. For further analysis we will assume T $_{\rm 1=f}$

Cooling by applying ux driving

For cooling we need to drive the system out of equilibrium. We propose to apply an external AC ux, x(t) = $_{\rm x;0}$ + D $_{\rm 0}$ cos! dt, to the qubit. As we operate at the special point where $\rm 0E_{\rm J}=0$ x = 0, linear driving is in possible. In the quadratic order, we obtain E $_{\rm J}$! E $_{\rm J}$ + (D=2) $^{\rm 2}$ E $_{\rm J}$ (cos2! dt + 1). This gives

$$H = \frac{E_J +}{2} z \frac{X}{2} x + h!_0 a^{y} a$$

$$+ (a^{y} + a) x \frac{Z}{2} cos2!_d t; (12)$$

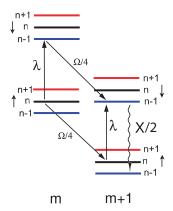


FIG. 3: The cooling process.

 $2h!_dm$, an unbound staircase of states appears. Each step of the staircase (F loquet zone) is characterized by a number m and spans the H ilbert space jijni. The neighboring zones are shifted by energy $2h!_d$ relative to each other. The states jijnijm i are the eigenstates of the H am iltonian

$$H_0$$
 (E_T +) _z=2 + h!₀a^ya 2h!_dm: (13)

The other three terms form the perturbation

$$H^{0} = \frac{X}{2}_{x} + (a^{y} + a)_{x} - \frac{1}{2}_{z} \cos :$$
 (14)

This perturbation H 0 causes transitions inside of each zone and also down and up the staircase. At nite (nonin nite) temperature of the bath the down transitions prevail and the system propagates down the staircase. This corresponds to the ow of energy from the driving source to the bath. During this ow, the driving source quanta of energy can be up-or down-converted in frequency by amount $!_{0}$, that is, photons with frequency $2!_{d}$ $!_{0}$ are emitted into the bath. The former case corresponds to cooling while the latter to heating.

We rst consider the up-conversion cooling process shown in Fig. 3. We choose the optimal detuning so that $2!_d = E_J + !_0$ and the levels J^{T} ; n; m i and J^{T} ; n; m i are degenerate (in what follows we use the units h = 1 for brevity). Thus we have to be careful when calculating the rates. First, we obtain the second order m atrix element between these two states equal to

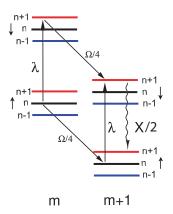


FIG . 4: The heating process.

 $p \frac{1}{n}$ where

$$\frac{1}{2E_{T}}:$$
 (15)

Note that the two paths shown in Fig. 3 interfere constructively. Then, the cooling rate depends on the relation between $\frac{1}{n}$ and $\frac{1}{r}=2$. For the weak driving case $\frac{1}{n}$ of $\frac{1}{r}=2$ we have the cooling rate $\frac{1}{n+n-1}$ (4 $\frac{2}{r}=\frac{1}{r}$) $\frac{1}{r}=1$ (the superscript is to emphasize that this rate is due to the driving). To justify this result we consider this process as tunneling from the level $\frac{1}{r}$; $\frac{1}{r}$; $\frac{1}{r}$ in to the broadened level $\frac{1}{r}$; $\frac{1}{r}$; $\frac{1}{r}$ in $\frac{1}{r}$ i

$$n! \ n \ 1 = 2 \ ^2 n \ \frac{1}{2} \text{ Im } G^R \ (! = 0)$$

$$= \frac{4^2}{2} n : \tag{16}$$

In the opposite, strong driving case, p = 1, there are coherent oscillations between the two levels. The appropriate description is then to say that doublets of new eigenstates, are formed which are split in energy by p = 1, see Fig. 5. The doublets are defined for p = 1 as p = 1, p = 1,

$$_{n + n - 1} = (4^{-2} - _{r}) n$$
 if $p = \frac{n}{n} < _{r} = 2$: (17)

Note that in the strong driving regime n denotes the doublet rather than the oscillator's level (see discussion below).

In addition to cooling, the AC driving induces competing heating processes. One, shown in Fig. 4, is a standard in quantum optics o resonance process. Indeed,

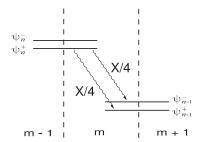


FIG. 5: Level structure of the strong driving for ac cooling. Here $_n$ (\dot{n} ;" \dot{i} \dot{n} 1;# \dot{i})= $\overline{2}$.

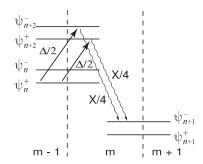


FIG. 6: Level structure of the strong driving for ac heating. The two shown processes interfere constructively.

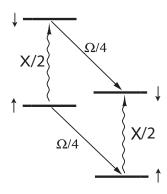
the states j";n;m i and j#;n+1;m+1i are connected in the second order by the matrix element n+1. These states are o resonance (we restrict ourselves to the values of n such that level splitting $2!_0$ n+1). Thus, in the case n < r=2 we obtain r=1 r=2 we obtain r=1 r=2 we use again the basis of doublets, Fig. 6, and arrive at r=1 r=1

$$_{n! \ n+1} = \frac{^{2}}{4! _{0}^{2}} _{r} (n+1)$$
 $\frac{1}{\frac{1+_{n,0}}{2}}$ if $\frac{p}{n} < _{r} = 2$: (18)

A nother driving-induced heating process, not characteristic for quantum optics, is due to the fact that in solid state systems there is strong noise at low frequencies (1=f noise). Thus, processes like the one shown in Fig. 7 become relevant. This process excites the qubit with the rate

$$e = \frac{2}{4E_J^2} \frac{hX_{!=!_0}^2 \dot{i}}{4h^2} : \qquad (19)$$

Since at $! = !_0$ the noise is dom inated by the 1=f contribution, rate (19) m ight dom inate the heating. W ith this process, the heating is also resonant and, in analogy



m m+1

FIG. 7: Qubit heating induced by the applied drive.

to Eq. (17), still assum ing that
$$_{e}$$
 r, we obtain $_{n-1!\ n} = \begin{array}{cccc} & & & & & & & & \\ & & & & & & \\ & & & & & \\ & & & & & \\ & & & & & \\ & & & & \\ & & & & \\ & & & & \\$

M aster equation. Taking into account the internal dissipation of the resonator with quality factor $\mathbb Q$, one can [5] write down them aster equation for the probability P_n to not the resonator in the state jni. First, we analyze the (strong driving) limit, $> \quad_{r}=2$. Then, it is convenient to write the rate equation in terms of the probabilities D_n to not the system in the doublet $_n$ (n 1). The probability D_0 , then, is the for the system to be in the (non-degenerate) ground state $_0=J^n;0$ i. The probabilities P_n are given by

$$P_n = \frac{1}{2} (D_n + D_{n+1}) + \frac{1}{2} D_{n n;0}$$
 (21)

The master equation reads

$$D_{n} = \frac{1}{2} {r \choose n+1} D_{n} (1 - n_{i0})$$

$$+ \frac{2}{8! \binom{2}{0}} {r \choose n} D_{n-1} (1 + n_{i1}) (n+1) D_{n} (1 + n_{i0})$$

$$+ \frac{1}{2} {e \choose n-1} (1 - n_{i0}) (1 + n_{i1}) D_{n} (1 + n_{i0})$$

$$+ \frac{! {0 \choose n} (! {0 \choose 0} + 1)}{Q}$$

$$+ \frac{! {0 \choose n} (! {0 \choose 0}) + 1}{Q} n \frac{1}{2} D_{n-1} (1 - n_{i0})$$

$$+ \frac{! {0 \choose n} (! {0 \choose 0})}{Q} n \frac{1}{2} D_{n-1} (1 - n_{i0}) (1 + n_{i1})$$

$$+ \frac{1}{2} D_{n} (1 + n_{i0}) : (22)$$

The unusual form of the second part of this master equation is due to the structure of the matrix elements between the di erent states of the doublets.

Multiplying Eqs. (22) by and sum m ing over n we obtain

$$\frac{d}{dt} \text{fmi} = \frac{1}{2} r(1 \quad D_0) + \frac{1}{2} e(1 + D_0) + \frac{2}{8!_0^2} r(1 + D_0)$$

$$\frac{!_0}{Q} \frac{2}{8!_0^2} r \text{fmi} + \frac{!_0}{2Q} (1 \quad D_0) + \frac{!_0 n_B (!_0)}{Q};$$
(23)

where hai $_{\rm n}^{\rm P}$ nD $_{\rm n}$. We rewrite the RHS of Eq. (23) in terms of the phonon occupation expectation value

$$\text{hni} = \sum_{n=1}^{x^2} nP_n = \sum_{n=1}^{x^2} (n - \frac{1}{2})D_n = \text{hri} - \frac{1 - D_0}{2}$$
: (24)

We, then, obtain

$$\frac{d}{dt} \ln i = \frac{1}{2} r(1 - D_0) + \frac{1}{2} e(1 + D_0) + \frac{2}{16! \frac{2}{0}} r(3 + D_0) + \frac{!_0}{Q} \frac{2}{8! \frac{2}{0}} r \ln i + \frac{!_0}{Q} n_B (!_0) :$$
(25)

There are two main cooling regimes in (25). If the coe cient in front of hni is positive, i.e., if ! $_0$ =Q (2 =8! $_0^2$) $_r$, we obtain the usual cooling with the cooling rate slow ing down with decreasing hni. As this is the relevant regime for realistic parameters we will analyze only this case. Interestingly, however, in the opposite case of very high Q, when ! $_0$ =Q (2 =8! $_0^2$) $_r$, the cooling rate accelerates until hni 1.

If hai $\,$ 1 (to be checked for self-consistency) the probability to be in the ground state is negligible, D $_0$ $\,$ 1. Then

hni
$$n_B (!_0) = \frac{(r_B)Q}{2!_0}$$
: (26)

This regime, thus, is realized when $n_B(!_0) > (r_e)Q = (2!_0)$. Clearly, for at least some cooling we need $(r_e)(2!_0) = Q$. At lower temperatures, Eq. (26) gives negative hniwhich means that the approximation breaks down and hni 1 or less. Then, for an estimate we can use 1 D_0 hri. In this regime hri 2hni (see Eq.(24)), therefore 1 D_0 2hni. Thus, for r_e

hni
$$\frac{e^{+\frac{!_0n_B(!_0)}{Q}}}{e}$$
: (27)

For n_B (!0) > $_{e}Q = !_{0}$ we then obtain

mi
$$\frac{!_0 n_B (!_0)}{Q_r}$$
; (28)

while in the opposite case the average occupation saturates at

$$mi - \frac{e}{r}: \qquad (29)$$

From Eq. (23) it is clear that for n_B (!0) 1, the cooling is initially exponential in time, $\ln i_t$ n_B (!0) $_{\rm r}Q=(2!_0)$ [1 exp(t)], with the decay rate determined by the oscillator bare damping, = !0=Q . Only when the low occupancy regime ($\ln i_t$ < 1) is reached, the rate of exponential decay increases to

$$=\frac{r}{2}\frac{e}{20};$$
 (30)

If the driving is weaker, then for some low values of n the following master equation holds (see Refs. [3, 5])

$$P_{n} = A + \frac{!_{0} (n_{B} (!_{0}) + 1)}{Q} [(n + 1)P_{n+1} nP_{n}] + A_{+} + \frac{!_{0}n_{B} (!_{0})}{Q} [nP_{n-1} (n + 1)P_{n}]; (31)$$

where A $4^2 = r$ and A₊ $(=2!_0)^2 r + e (4^2 = r^2)$. For the average occupation number hni in the stationary state we obtain

$$mi = \frac{A_{+} + \frac{!_{0} n_{B} (!_{0})}{Q}}{A \quad A_{+} + \frac{!_{0}}{Q}} :$$
 (32)

Regim es sim ilar to Eqs. (28) and (29) are clearly identied. However, a regim e sim ilar to Eq. (26) is not possible within master equation (31). The expression for the oscillator occupancy Eq. (32) can be naturally interpreted in terms of two independent heat baths acting on the resonator, one being the equilibrium environment at the nominal external temperature T, coupled to the resonator by a coupling strength $_0 = !_0 = Q$, while the other bath being introduced by the cooling process itself. The elective temperature of the latter, T, can be dened through A $= A_+ = \exp(!_0 = T)$, and the elective coupling strength is $= !_0 = Q = A$ A₊. Then, the nal resonator occupancy can be re-expressed as

$$mi = \frac{{}_{0}n_{B} (!_{0}) + n_{B} (!_{0})}{{}_{0} +};$$
 (33)

where n_B is the Bose distribution function at temperature T . Clearly, T is the lowest possible temperature for a given cooling process, which is achieved for 0. The combined damping coe cient 0+ determines the rate of relaxation to the new stationary state.

Example. We consider a nanom echanical resonator with fundamental frequency 100 MHz (! $_0$ = 2 100 MHz = 0.5 eV) and quality factor Q = 10^5 . It is coupled to the qubit, which is characterized by the Josephson energy E $_{\rm J}$ 50 eV and Coulomb charging

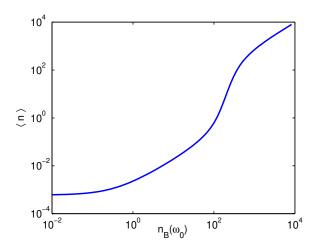


FIG.8: Cooling diagram for a 100 M H z resonator (detailed parameters in text).

energy E $_{\rm C}$ $\,$ 160 eV (corresponds to C $\,$ 500 aF). The coupling strength between the resonator and the qubit is determ ined by the mutual capacitance C $_{\rm X}$ $\,$ 20 aF, and the gate voltage V $_{\rm X}$ $\,$ 1 V, such that n $_{\rm X}$ $\,$ 60 C coper pairs (see Ref. [8]). The gap between the resonator and the CPB is d $\,$ 100 nm . For these parameters, from Eq. 4, the resonator-CPB coupling strength is 0:1 eV . Assum ing that C $_{\rm G}$ < C $_{\rm X}$, for the relaxation rate of CPB we nd $_{\rm r}$ = 3 $\,$ 10 3 eV .

The circuit-induced quality factor of the resonator is $Q_{em}=4$ flowhich is signi cantly higher than the quality factors of typical resonators. For the 1=f contribution at $T_{1=f}>10\,!_0$ we obtain $Q_{1=f}>10^7$, which is still higher than a typical value. Hence this modi cation of the oscillator damping can be neglected compared to other environmentale ects.

For cooling, we take 1 eV, which corresponds to the modulation depth D = 0:1. We thus obtain 10 3 eV, and hence for all n we have $\stackrel{P}{n} >$ =2 and $_{\rm n\,!\,n}$ $_{\rm 1}$ $_{\rm r}$ =2 (strong driving regin e). The heating is indeed dom inated by 1=f noise, with $_{\rm e}$ = (=2E $_{\rm J}$)² (E $_{\rm 1=f}^2$ =4! $_{\rm 0}$) 1:8 10 eV. In this regin ewe get the following results for cooling:

The exact numerical solution of the rate equations Eq. (22) is shown in Figure 8.

Cooling by applying voltage driving

A notherway to achieve AC cooling is by applying radio frequency voltage bias to the gates. In Fig. 1, apply a driving voltage $V_x = V_0 \cos !_d t$ on the resonator and another driving voltage $V_g = (C_x = C_g)V_x$ on the CPB.

The ac voltage V_x generates resonant coupling between them echanical resonator and the CPB when $!_{ac} = E_J$ $!_0$, which corresponds to the rst red sideband coupling in quantum optics. The voltage V_x also generates an oscillating charge bias on the CPB with $N_g^x = C_x V_x = 2e$; however, it is balanced by the bias V_g , which prevents harm fulac pumping of the CPB.

The scheme. The Ham iltonian of the voltage driving scheme is

$$H = \frac{E_{J}}{2} z + h!_{0} \hat{a}^{y} \hat{a} + 4E_{c} n_{g} x$$

$$+ \cos!_{d} t \hat{a}^{y} + \hat{a} x \frac{\hat{x}}{2} x \qquad (34)$$

where the qubit works at the optim alpoint of $n_g = 0$ to avoid the 1=f noise. The coupling is

$$= 4E_{c} \frac{C_{x}V_{0}}{2e} \frac{x}{d} :$$
 (35)

Sim ilar to the ac ux driving setup, we analyze the side-band cooling (! $_0$; $_r$) in the regimes of weak driving and the strong driving; both can be reached in experiments.

The analysis is essentially the same as that in the ux driving case. Instead of the second order matrix element (see Eq. (15)), we have the direct coupling =2. Thus to obtain the cooling and the heating rates we substitute! =2 into Eqs. (17) and (18). In this scheme there is no driving induced contribution of the low frequency (1=f) noise similar to (20).

Strong driving. The strong driving regin e is achieved for \overline{n} =2 $_r$ =2. As the 1=f noise does not contribute to the heating, i.e., the rates (20) do not appear, the leading heating mechanism is the o-resonance coupling (see Eq. (18)). Thus, the dynam ics is described by the rate equation (22) with $_e$ = 0. We obtain the cooling results as follows: For n_B > Q ($_r$ =2! $_0$) we obtain hni n_B Q ($_r$ =2! $_0$). In the interm ediate regin e Q ($_r$ =2! $_0$) > n_B > Q ($_r$ =1! $_0$) (=4! $_0$) 2 the result is hni !0 n_B =Q $_r$. Finally, for n_B < Q ($_r$ =! $_0$) (=4! $_0$) 2 , the occupation number saturates at hni (=4! $_0$) 2 .

For exam ple, let $_{\rm r}=5$ 10^3 eV , =25 10^3 eV (with the voltage bias V_0 $50\,{\rm m\,V}$) and Q = 10° . We have (=4!_0)^2 $_{\rm r}$ 8 10° eV . The stationary occupation number is

which gives hni=2.5 10^3 at the tem perature of 20 m K. Weak driving. For n=2 $_r=2$, the dynamics of the resonator is described by the rate equation (31) with A = 2 = $_r$ and A₊ = $(=4!_0)^2$ $_r$. Note that the low frequency noise doesn't appear in this scheme ($_e=0$), which improves the cooling e ciency. For

 $n_B~(!_{\,0})$ < $A_+~Q=!_{\,0}$ the average occupation is given by $hn\,i=A_+=\!\!A$; for $n_B~(!_{\,0})>A_+~Q=!_{\,0}$ we obtain $hn\,i=n_B~(!_{\,0})!_{\,0}=\!\!A$ Q . As an example, let $_r=50~10^3$ eV , $=5~10^3$ eV (with the bias voltage of $V_0~10\,m$ V) and Q = 10^5 . We have A = $0.5~10^3$ eV and $A_+=3~10^7$ eV . Then, the cooling results are as follows:

$$\text{hni} = \begin{cases} 10^{-2} n_{\text{B}} (!_{0}); & n_{\text{B}} (!_{0}) > 0.06 \\ 6 & 10^{4}; & n_{\text{B}} (!_{0}) < 0.06 \end{cases}$$
(36)

where at the tem perature of 20 m K with n_B (! 0) = 5, we have hni=0.05. Thus better cooling can be achieved in the strong driving regime than that in the weak driving regime.

D iscussion. The relaxation rate $_{\rm r}$ can be adjusted by varying the external circuit of the CPB. For example, by varying the gate capacitance C $_{\rm g}$, the relaxation rate changes as $_{\rm r}$ / C $_{\rm g}^2$. The coupling constant can be adjusted by varying the bias V $_{\rm 0}$. In this scheme, we choose V $_{\rm 0}$ to be in the range of 10:::100 m V and $_{\rm r}$ in the range of (1:::100) $_{\rm r}$ 10 $_{\rm r}^3$ eV, which includes both the weak driving regime ($_{\rm r}^{\rm h}$ $_{\rm r}$ =2) and the strong driving regime ($_{\rm r}^{\rm h}$ $_{\rm r}$ =2). These parameter regimes have been realized in charge qubit experiments.

One practical issue of this scheme concerns the accuracy of the gate compensation. Both gate voltages generate an extra part of the CPB's charging energy H = $4E_c$ n_g x, with n_g = $(C_xV_x + C_gV_g)$ =2e. By controlling the voltage with an accuracy of microvolts, which can be achieved with standard technology, the oscillating bias on the CPB can be neglected.

Compared with the ac ux driving cooling scheme in this paper, the resonator can now be cooled to a lower temperature because the heating process only involves the electrom agnetic noise of the circuit at frequency E $_{\rm J}$, while the low frequency noise, which is the dominant heating factor in the previous scheme, doesn't a ect the system .

DC COOLING

E ectively, AC driving can be achieved applying a DC transport voltage to an auxiliary Josephson junction. We modify the system as shown in Fig. 9 so that it becomes e ectively an SET transistor. Dissipative Cooper pair and quasi-particle transport is similar systems was considered in Refs. [11, 12]. The Hamiltonian in the charge hasis reads

$$H = \frac{(Q \quad C_R V \quad C_g V_g \quad C_x (x) V_x)^2}{2C}$$

$$E_{J;L} \cos \quad E_{J;R} \cos(+ 2eV t=h) + H_x ; (37)$$

where is the phase on the island (and simultaneously on the left junction as the left lead is grounded), C

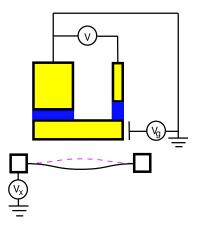


FIG. 9: The system with DC driving.

 C_{L} + C_{R} + C_{g} + C_{x} (x). Due to the transport voltage V , the H am iltonian is time dependent and, thus, represents a driven system . We repeat the steps described above and arrive (in the charge basis) at

$$H = \frac{E_{J;L}}{2} \times \frac{X}{2} z + h!_{0}a^{y}a + (a^{y} + a) z$$

$$\frac{E_{J;R}}{2} (_{+} e^{i!_{J}t + i} + hx;); \qquad (38)$$

where K $\frac{4E_c}{e}$ (C_R $V + C_g$ $V_g + C_x$ V_x), (2e=h) V dt, and the Josephson frequency $!_J$ 2eV=h. We see that the right junction's Josephson energy assumes the role of pumping amplitude , while $!_J$ is the pumping frequency. Unfortunately V is noisy and, thus, the pumping source has a substantial line-width. The transport voltage should not be sensitive to the background charges, therefore V is assumed to have 0 hm ic noise spectrum (no 1=f component).

A fler a =2 rotation in the x $\,$ z plane, $_{x}$ \$ $_{z}$, we obtain

$$H = \frac{E_{J;L}}{2} z \frac{X}{2} x + h!_{0}a^{y}a + (a^{y} + a) x$$

$$\frac{E_{J;R}}{4} (z + i_{y})e^{i!_{J}t+i} + hx: : (39)$$

While the Hamiltonians (12) and (39) look similar, there are two important dierences. One, already discussed, is the fact that the pumping frequency $!_J$ in (39) is fundamentally noisy, while $!_d$ in (12) can be made coherent. The second (very important) dierence is that in (12) the pumping is applied to $_z$ only, while in (39) it couples to $_z$ and $_y$. Both these facts hinder the cooling. Indeed, the coupling to $_y$ gives a direct matrix element $E_{J;R}$ =4 between the states J; n; m i and J; n; m + 1i. This interaction repels the levels and we must choose $E_{J;R}$ 4! $_0$ so that the resonant detuning as in Fig. 3 is possible. In addition, the noise of the transport voltage translates into the line width for the transition J"; n; m i ! J; m; m i ! J; m + 1i equal to

, = 2 $_{\rm tr}k_{\rm B}\,T$ = h, where $_{\rm tr}$ R = $R_{\rm Q}$. The uctuations of the transport voltage are not screened by the ratio of capacitances as it happens for the gate charge. Therefore $_{\rm tr}$ 10 2 . Because of these additional constraints the applicability of the DC cooling scheme is limited to higher frequency/quality factor resonators. For an estim ate, consider an oscillator with $!_0 = 2$ 50 mK at temperature T = 50 mK.W e then 0:3 eV, which signicantly exceeds r. obtain , Hence, we have to substitute r by in all form ulas. For the Josephson coupling in the right junction we take $E_{J;R} = 2$ eV. Then, instead of Eq. (15), we nd $E_{J:R} = (2E_{J:L})$ 2 10° eV (we assum $e_{J:L}$ 50 eV). The cooling rate can again be represented as $2^2 = 7$, $2 \cdot 10^6$ eV. Thus, cooling A n, where A becomes possible only if $Q > !_0 = A$

D ISCUSSION AND COMPARISON WITH QUANTUM OPTICS.

For com parison with quantum optics cooling schemes, we present here an analysis of some of the processes described above using the quantum optics language. In quantum optics literature one usually employs the transformation to the rotating frame and/or other canonical transformations together with the Rotating W ave Approximation (RWA) in order to single out the near resonant terms responsible for the studied transitions. We start with Hamiltonian (12) and transform it into the interaction representation with respect to H $_{\rm 0}$ (t)

$$[E_J + + \cos 2!_d t]_z = 2 + !_0 a^y a$$
. This amounts to

$$_{+}$$
 ! $_{+}$ e $^{i(E_{J}t+}$ $^{t+}$ $^{\frac{1}{2!}}$ $^{sin 2!}$ and a ! ae $^{i!}$ 0t :

As $2!_d$ E_J we can expand the factor $\exp(i(=2!_d)\sin 2!_d t)$. The near resonant (RWA) parts of the coupling term H $(A' + a)_x$ read, then, after the transform ation as

$$H^{RWA} = \frac{1}{4!_d} (a + a^y e^{2!_0 t} + h x;);$$
 (41)

where the resonance condition $2!_d = E_J + !_0$ was assumed. The rst term of (41) clearly corresponds to the resonant transition provided by the matrix element $\frac{p}{n}$ (see Eq. (15)). The second term corresponds to the o-resonant transition. In analogy with atom optics [3], we can introduce Lamb-Dicke parameter $=2!_d$ $=E_J$. Note that, unlike the case of trapped atom s/ions we do not have near resonant terms ipping just the spin, exp ($i!_0$). Such an interaction would repel the levels, and, for a resonant detuning, one would need $!_0$. In our case, a much stronger driving is allowed. We do, however, encounter this limitation in the DC cooling

scheme due to the presence of the near-resonant term in

the Hamiltonian Eq. (39) which is proportional to $_{\rm V}$.

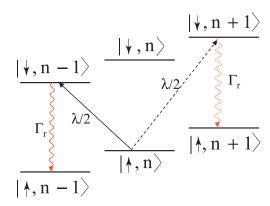


FIG. 10: Level structure of the voltage driving scheme for ac cooling. The solid lines indicate the cooling process; and the dotted lines indicate the heating process.

A lso, in the dissipative term H_X (X =2)_x, we nd a slow contribution:

$$H_X^{\text{slow}} = \frac{X}{2} \frac{1}{4! d}$$
 $e^{i! ot} + h x$: ; (42)

which is responsible for the heating process (18) dominated by the low frequency noise. In quantum optics this contribution is typically neglected as there are no strong low frequency sources.

In the case of ac voltage cooling, in the rotating wave approximation the Hamiltonian is

$$H^{RWA} = \frac{h!_0}{2} z + h!_0 \hat{a}^{y} \hat{a}$$

$$+ \frac{1}{2} \hat{a}^{y} + \hat{a} + \hat{a}^{y} + \hat{a}_{+} \qquad (43)$$

$$\frac{\hat{X}}{2} + e^{i!_d t} + e^{i!_d t}$$

where the interaction includes the resonant coupling $\hat{a}^y_+ + \hat{a}_-$ between the states j'';ni and j'

The voltage driving scheme for ac cooling presents a direct analogue to the laser cooling of quantum optics systems as is obvious from Fig. 10; however, it is a simpler scheme as the coupling is a direct bilinear coupling instead of the polaron coupling in quantum optics.

\DOPPLER " COOLIN G

For smaller oscillator frequencies $!_0$ and/or larger qubit relaxation rates $_{\rm r}$, it may happen that the vibrational sidebands are no longer resolved, i.e., $_{\rm r} > !_0$. Then, cooling to the ground state is in possible but the

less e ective \D oppler" cooling is still feasible. In the standard Doppler cooling, cold atom smoving in a laser eld experience di erent light pressure depending on their velocity. For instance, if the laser is red-detuned relative to the atom ic transition, then atom moving towards the light source will be absorbing photons more than an atom moving away from the source, which will result in a velocity-dependent force on the atom. By properly arranging multiple lasers it is then possible to achieve signi cant reduction of the atom 's e ective tem perature. The same reasoning applies to an atom in a trap, when the trap frequency is much smaller than the atom ic transition line width. Equivalently, in this case, the Doppler cooling can be reinterpreted in terms of the cooling and heating transition rates for the oscillating atom. For red-detuned laser, photon absorption processes with simultaneous phonon emission dominate the ones where an additional phonon is created. One can show that, sim ilar to the free atom case, this leads to cooling down to temperatures proportional to the atom ic transition line width. In this section we will demonstrate that an analog of Doppler cooling can be performed in both AC and DC cooling setups described in the previous sections in the regime of non-resolved sidebands.

AC cooling scheme. We start with the AC-driving scheme described by Hamiltonian (12). In the Doppler case it is enough to study, rst, the spin's dynamics without the oscillator. We perform the following transform attion

$$_{+}$$
! $_{+}$ e $^{i(2!_{d}t+\frac{1}{2!_{d}}\sin 2!_{d}t)}$; (44)

and keep only the RW A term s in the coherent part of the H am iltonian but all the term s in the part describing the interaction w ith the bath. The transform ed H am iltonian reads

$$H_{spin}^{RWA} = \frac{!}{2} z \frac{X}{2} (_{+}e^{_{2i!}dt} + hx;) + \frac{X}{4!_{d}} \frac{X}{2} x;$$
(45)

where ! is the detuning ! 2_d E_J . The last term in the Ham iltonian, as before (see Eqs. (19) and (18)), generates transitions between the ground and excited states of the qubit. The corresponding rate, however, is typically much smaller than the relaxation rate generated by the second term of the Ham iltonian, and hence can be neglected. This is in contrast to the AC ground states cooling scheme discussed above, where the qubit heating rate determined the lowest possible occupation number of the resonator. The slow (RWA) part of the interaction Ham iltonian reads

$$H^{slow} = \frac{1}{4!_d} (a^y + a)_x :$$
 (46)

W ith Ham iltonian (45) we write down the B loch-Red eld equations [13, 14] for the spin's density matrix $_=R$,

where R is the Red eld tensor. In this equation, the density matrix is treated as a four-vector. We choose the representation = $(1=2)s_0 + _z + _+ + _$, which gives = $(s;\;;\;)$ and Tr = s. For proper density matrices s=1. In this representation

$$R = \begin{bmatrix} 0 & 0 & 0 & 0 & 0 & 1 \\ B & \frac{r}{2} & r & 0 & 0 & C \\ 0 & 0 & 0 & i! & \frac{r}{2} & 0 & A & : \\ 0 & 0 & 0 & i! & \frac{r}{2} & 0 & A & : \end{bmatrix}$$
(47)

The rate $_{\rm r}$ originates from the second term of (45),

$$r = \frac{hX_{!=2!d}^{2} \dot{i}}{4h^{2}}; (48)$$

(cf. Eq. 7). For sim plicity we have assumed that at high frequency 2! d the temperature is electively zero, i.e., $hX_{!=2!d}^2$ i $hX_{!=2!d}^2$ i.

Next we employ the \quantum regression theorem " (approxim ation) to obtain (for t > 0) the correlator

$$C_{x}(t) = h_{x}(t) \times (0)i = Tr_{x} e^{Rt} \times (49)$$

where $_1$ is the stationary density matrix, R $_1$ = 0. For t < 0 we can use C $_x$ (t) = C $_x$ (t). In the four-vector representation the operator $_x$ multiplying from the left is given by

$$x = \begin{bmatrix} 0 & 0 & 0 & 1 & 1 \\ B & 0 & 0 & 1 = 2 & 1 = 2C \\ B & 1 = 2 & 1 & 0 & 0 & A \end{bmatrix}$$
(50)

Finally, after the Fourier transform we obtain

$$C_x(!) = 2ReTr_x[R + i!]^1_{x=1}$$
; (51)

which is easy to calculate (using M athem atica). Expanding near! = 0 we obtain C_x (!) = $S_x + x!$, where

$$S_{x} = \frac{4 r}{4 !^{2} + \frac{2}{r}}; (52)$$

and

$$_{x} = \frac{32 ! r}{(4 !^{2} + \frac{2}{r})^{2}} :$$
 (53)

From the spin correlation functions, we can now determ ine the transition rates for the resonator, A = $(=4!)^2C_x(=!_0)$. Note, that the same expressions for A can be obtained from Eq. (16) generalized to arbitrary detuning. Then, the secondary \heat bath" introduced by cooling is characterized by the e ective temperature

$$T \qquad \frac{S_x}{2_x} = \frac{4 !^2 + \frac{2}{r}}{16 !} : \qquad (54)$$

Optim izing with respect to the detuning !, we not that the minimum (positive) temperature T_{min} =4 is reached for the optimal red detuning !opt r=2. For the elective quality factor due to the spin we obtain

$$\frac{1}{Q} = \frac{A}{!_0} = \frac{A_+}{8!_d^2} : \tag{55}$$

The nalresonator occupancy can now be obtained from Eq. (33). Clearly, Q must be smaller than the oscillator's own quality factor in order for cooling to be elective. For the same parameters as used in the AC cooling section, we not that at the optimal detuning Q 1, which corresponds to a nearly overdam ped regime, similar to optical molasses in atom optics. Hence, a resonator with a frequency $!_0 \le r=2=300 \ \rm kHz$ can be cooled down to temperature $T_{\rm min} r=4=10 \ \rm K. Note$, that the elect of the dominant qubit heating mechanism due to the l=f noise, which we neglected here, if necessary, can be managed by reducing the driving strength (at the expense of reduced cooling power, i.e. larger Q).

Sim ilar analysis applies to the voltage driving scheme for AC cooling in the Doppler regime. For $\frac{P}{n}=2$ =2, from Eq. (16)

$$A = \frac{{2 \choose r}}{{2 \choose r} + 4 (! + !_0)^2} \quad A_+ = \frac{{2 \choose r}}{{2 \choose r} + 4 (! !_0)^2};$$
(56)

where $!=!_d$ E_J is the detuning of the driving frequency from the qubit's ground-to-excited-state transition. Cooling is achieved when !<0. Neglecting the e ect of the nite intrinsic Q-factor, the nal phonon number from Eq. (32) is

The scheme provides optimal cooling at $!_{opt} = r=2$ with the temperature $T_{m \ in} = r=4$, same as the ux driving case.

DC cooling scheme. Analysis of the DC cooling scheme proceeds analogously. We start with Hamiltonian (39) and perform transformation

$$_{+}$$
! $_{+}$ e $^{i(!_{J}t+}\frac{}{!_{J}}\sin !_{J}t)}$; (58)

where, for now, $E_{J,R}$, and we rem ind that $!_J$ (2e=h)V. For simplicity we consider V noiseless now but later will introduce the low-frequency (classical) noise of V. Then, we obtain

$$H_{spin}^{RWA} = \frac{!}{2} z \frac{1}{4} x$$

$$\frac{X}{2} (_{+}e^{Vt} + hx;) + \frac{X}{2V} \frac{X}{2} x; (59)$$

where ! I_J $E_{J;L}$. The main dierences with (45) are: i) the second term of (59) is absent in (45) (recall

the extra m atrix element in the DC scheme); ii) the detuning ! is noisy due to the noise of V . This will give an extra \pure" dephasing rate $\ = 2 \ _{\rm tr} k_B T = h$, where $\ _{\rm tr} \ R = R_Q$. As in the AC Doppler case, neglecting the excitation rate coming from the last term in the H am iltonian, for the Red eld tensor we obtain

$$R = \begin{bmatrix} 0 & 0 & 0 & 0 & 1 \\ B & \frac{r}{2} & r & \frac{i}{4} & \frac{i}{4} & C \\ 0 & \frac{i}{2} & i ! & 0 & A \\ 0 & \frac{i}{2} & 0 & i ! & 2 \end{bmatrix}$$
(60)

where ~= , + $_{\rm r}$ =2. The general expressions for S_x and $_x$ are quite complicated. An analysis shows that the simplest cooling regime is achieved when $_{\rm r}$,. That is, it does not make sense to keep small $_{\rm r}$ when the line width is anyway given by large ,. The relaxation rate $_{\rm r}$ can easily be increased by choosing bigger gate capacitances C_x and/or C_g . A ssum ing $_{\rm r}$ = , and , we obtain

$$S_{x} = \frac{12 \ ,}{4 \ !^{2} + 9 \ ?} ; \tag{61}$$

and

$$_{x} = \frac{96 ! ,}{(4 !^{2} + 9 ?)^{2}} :$$
 (62)

Optim izing with respect to $\,!$, we not that the m in im um tem perature $T_{\text{m in}}$ $\,$ (3=4) , is achieved for the optim all detuning $\,!$ $\,$ (3=2), . The elective quality factor due to the cooling environment, similarly to (55), is

$$\frac{1}{Q} = \frac{{}^{2} {}^{2} {}^{x}}{2! {}^{2}_{J}} : \tag{63}$$

The regime $_{\rm r}$, is more subtle and requires further analysis.

Example: Choosing C_x 200 aF instead of previously assum ed 20 aF, we obtain r 0:3 eV . We choose 0:1 eV (note that this is quite a sm all value for usual Josephson junctions). Then we obtain $T_{m \ in}$ 2:5 m K for ! 0:5 eV 2 $6 (eV)^{2}$. Near optim aldetuning point, we obtain x For the coupling constant we can take 1 eV instead of 0:1 eV as we have allowed ten times bigger capacitance C_x . Then we obtain Q0:8 10 Thus, for cooling to be e ective, resonator Q -factor should exceed 10⁵ and the nal resonator temperature is determined according to Eq. (33) with T = 2.5 K.

CONCLUSIONS

We considered several approaches to active cooling of mechanical resonators using a coupling to a superconducting Josephson qubit. In the resolved vibrational

sideband regime, when the qubit level width is smaller than the resonator frequency, we proposed two schemes for ground-state cooling of the resonator. In the rst scheme, the AC driving required for cooling is provided by an external microw ave source. We not that for a 100 MHz oscillator coupled to a practically realizable Josephson qubit, at the external tem peratures below $1 \; \text{K}$, it is possible to reduce the therm aloccupancy of the oscillator m ode by three order of magnitude. In the second scheme, the AC driving is generated by the AC Josephson oscillations on an auxiliary junction of the qubit. This scheme is attractive since there is no need for an external AC driving source; however, in the present realization, we nd that it is not as e ective as the one with an explicitly applied AC driving. We also demonstrate that even in the regime when the vibrational sidebands are not resolved, it is possible to perform an analogue of Doppler cooling with the nal resonator temperature limited by the qubit line width.

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